

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	29	(light adj emitting) and (light adj receiving) and (silicon adj substrate) and (doped adj region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 18:20
L2	0	(light adj transporting) and (light adj receiving) and (silicon adj substrate) and (doped adj region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 16:27
L3	5	(light adj transmitting) and (light adj receiving) and (silicon adj substrate) and (doped adj region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 16:27
L4	14	(light adj emitting) and (light adj absorbing) and (silicon adj substrate) and (doped adj region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 16:27
L5	221	(light adj emitting) and (photodetector) and (silicon adj substrate) and (doped adj region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 18:20
L6	6	(light adj emitting) and (light adj modulator) and (silicon adj substrate) and (doped adj region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 16:27
L7	28	(laser) and (light adj receiving) and (silicon adj substrate) and (doped adj region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 17:32
L8	0	(vcsels) and (light adj receiving) and (silicon adj substrate) and (doped adj region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 16:26

L9	32	(light adj emitting) and (light adj receiving) and (silicon adj substrate) and (impurity adj region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 17:32
L10	0	(light adj transporting) and (light adj receiving) and (silicon adj substrate) and (impurity adj region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 16:27
L11	16	(light adj transmitting) and (light adj receiving) and (silicon adj substrate) and (impurity adj region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 18:31
L12	7	(light adj emitting) and (light adj absorbing) and (silicon adj substrate) and (impurity adj region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 16:27
L13	10	(light adj emitting) and (photodetector) and (silicon adj substrate) and (impurity adj region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 16:27
L14	0	(light adj emitting) and (light adj modulator) and (silicon adj substrate) and (impurity adj region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 16:27
L15	0	(light adj emitting) and (photodetector) and (silicon adj substrate) and (doped adj region) and (gto or (gate adj turn adj off adj thyristor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 17:18
L16	1	(light adj emitting adj device) and (light adj receiving adj device) and (photoelectric adj conversion) and (gto or (gate adj turn adj off adj thyristor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 17:19

L17	0	(light adj emitting) and (light adj receiving) and (silicon adj substrate) and (impurity adj region) and (gto or (gate adj turn adj off adj thyristor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 17:19
L18	0	(light adj emitting) and (light adj receiving) and (silicon adj substrate) and (doped adj region) and (gto or (gate adj turn adj off adj thyristor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 17:22
L19	2	"6806111".pn. and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 17:35
L20	0	"6806111".pn. and leakage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 17:25
L21	25	(light adj emitting) and (photodetector) and (silicon adj substrate) and (doped adj region) and (leakage adj current)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 17:32
L22	0	(light adj emitting) and (photodetector) and (silicon adj substrate) and (doped adj region) and (block near5 (leakage adj current))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 17:27
L23	0	(laser) and (light adj receiving) and (silicon adj substrate) and (doped adj region) and (block near5 (leakage adj current))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 17:27
L24	0	(light adj emitting) and (photodetector) and (silicon adj substrate) and (doped adj region) and (leakage adj current) and (block near5 (leakage adj current))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 17:27

L25	1	(light adj emitting adj device) and (light adj receiving adj device) and (photoelectric adj conversion) and (block near5 (leakage adj current))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 17:28
L26	1	(optoelectronic adj device) and (photoelectric adj conversion) and (block near5 (leakage adj current))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 17:28
L27	0	(light adj emitting) and (light adj receiving) and (silicon adj substrate) and (doped adj region) and (switch adj circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 17:29
L28	3	(light adj emitting) and (photodetector) and (silicon adj substrate) and (doped adj region) and (doped adj region) and (switch adj circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 17:29
L29	6	(light adj emitting) and (light adj receiving) and (silicon adj substrate) and (doped adj region) and (quantum and confinement)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 17:31
L30	14	(light adj emitting) and (photodetector) and (silicon adj substrate) and (doped adj region) and (quantum and confinement)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 17:31
L31	1	(laser) and (light adj receiving) and (silicon adj substrate) and (doped adj region) and (quantum and confinement)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 17:32
L32	4	(light adj emitting) and (photodetector) and (silicon adj substrate) and (doped adj region) and (leakage adj current) and (quantum and confinement)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 17:32

L33	0	(light adj emitting) and (light adj receiving) and (silicon adj substrate) and (impurity adj region) and (quantum and confinement)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 17:32
L34	1	(laser) and (light adj receiving) and (silicon adj substrate) and (doped adj region) and (quantum and confinement)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 17:32
L35	1	"6806111".pn. and silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 17:35
L36	6	(light adj emitting) and (light adj receiving) and (silicon adj substrate) and (doped adj region) and (monocrystalline adj (si or silicon))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 18:19
L37	5	(light adj emitting) and (light adj receiving) and (silicon adj substrate) and (doped adj region) and (two adj dimensional adj array)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 18:19
L38	5	(light adj emitting) and (light adj receiving) and (silicon adj substrate) and (doped adj region) and (two adj dimensional adj array)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 18:20
L39	19	(light adj emitting) and (photodetector) and (silicon adj substrate) and (doped adj region) and (two adj dimensional adj array)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 18:21
L40	0	"20020181915".pn. and (two adj dimensional adj array)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 18:21

L41	0	"20020181915".pn. and (2d adj array)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 18:21
L44	695	257/80.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 18:47
L45	1411	257/79.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 18:47.
L46	1075	257/82.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 18:47
L47	1973	257/103.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 18:48
L48	422	257/101.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 18:48
L49	591	257/102.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 18:49
S1	10	(light adj emitting adj device) and (light adj receiving adj device) and (photoelectrical adj conversion)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 16:04

S2	120	(light adj emitting adj device) and (light adj receiving adj device) and (photoelectric adj conversion)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 17:28
S3	2	(light adj emitting adj device) and (light adj receiving adj device) and (optoelectronic adj conversion)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 17:00
S4	2	"20030127655".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 16:51
S6	25	choi-byoung-lyong.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 16:19
S7	46	kim-jun-young.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 16:51
S8	58	lee-eun-kyung.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 16:20
S9	6	(optoelectronic adj device) and (light adj receiving adj device) and (photoelectric adj conversion)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 20:01
S10	39	(optoelectronic adj device) and (photoelectric adj conversion)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/18 18:46

S11	36	silicon adj optoelectronic adj device	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 17:57
S12	12	(silicon adj optoelectronic) and (light adj emitting) and (light adj receiving)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 19:07
S13	9	(silicon adj optoelectronic) and (light adj emitting) and (light adj receiving) and (silicon adj substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/17 19:07